



BDV67-A-B-C-D

NPN SILICON DARLINGTONS POWER TRANSISTORS

They are silicon epitaxial base transistors mounted in TO-3PN.
 They are designed for audio output stages and general amplifier and switching applications.
 complementary is BDV66-A-B-C
 Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings	Value	Unit	
V_{CEO}	Collector-Emitter Voltage	BDV67	60	V
		BDV67A	80	
		BDV67B	100	
		BDV67C	120	
		BDV67D	150	
V_{CBO}	Collector-Base Voltage	BDV67	80	V
		BDV67A	100	
		BDV67B	120	
		BDV67C	140	
		BDV67D	160	
V_{EBO}	Emitter-Base Voltage	BDV67	5.0	V
		BDV67A		
		BDV67B		
		BDV67C		
		BDV67D		
I_B	Base Current	BDV67	0.5	A
		BDV67A		
		BDV67B		
		BDV67C		
		BDV67D		
I_C	Collector Current	BDV67	16	A
		BDV67A		
		BDV67B		
		BDV67C		
		BDV67D		
I_{CM}		BDV67	20	
		BDV67A		
		BDV67B		
		BDV67C		
		BDV67D		



BDV67-A-B-C-D

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings			Value	Unit
P_T	Power Dissipation	@ $T_{mb} = 25^\circ C$	BDV67	200	W
			BDV67A		
			BDV67B		
			BDV67C		
			BDV67D		
T_J	Junction Temperature		BDV67	150	$^\circ C$
			BDV67A		
			BDV67B		
			BDV67C		
			BDV67D		
T_s	Storage Temperature		BDV67	-65 to +150	$^\circ C$
			BDV67A		
			BDV67B		
			BDV67C		
			BDV67D		

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-mb}	Thermal Resistance, Junction to Mounting Base	0.625	$^\circ C / W$

SWITCHING TIMES

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
t_{on}	turn-on time	$I_C = 10 A, V_{CC} = 12 V$ $I_{B1} = -I_{B2} = 40 mA$	-	1	-	μs
t_{off}	turn-off time		-	3.5	-	



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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)		Min	Typ	Mx	Unit	
I_{CEO}	Collector Cutoff Current	$V_{CE}= 30\text{ V}, I_B= 0$		BDV67	-	-	1	mA
		$V_{CE}= 40\text{ V}, I_B= 0$		BDV67A	-	-		
		$V_{CE}= 50\text{ V}, I_B= 0$		BDV67B	-	-		
		$V_{CE}= 60\text{ V}, I_B= 0$		BDV67C	-	-		
		$V_{CE}= 75\text{ V}, I_B= 0$		BDV67D	-	-		
I_{EBO}	Emitter Cutoff Current	$V_{BE}= 5\text{ V}, I_C= 0$		BDV67	-	-	5.0	mA
				BDV67A	-	-		
				BDV67B	-	-		
				BDV67C	-	-		
				BDV67D	-	-		
I_{CBO}	Collector-Base Cutoff Current	$I_B= 0$ $T_j=25^\circ\text{C}$	$V_{CB}= 80\text{ V}$	BDV67	-	-	1	mA
			$V_{CB}= 100\text{ V}$	BDV67A	-	-		
			$V_{CB}= 120\text{ V}$	BDV67B	-	-		
			$V_{CB}= 140\text{ V}$	BDV67C	-	-		
			$V_{CB}= 160\text{ V}$	BDV67D	-	-		
		$I_B= 0$ $T_j=150^\circ\text{C}$	$V_{CB}= 40\text{ V}$	BDV67	-	-	4	
			$V_{CB}= 50\text{ V}$	BDV67A	-	-		
			$V_{CB}= 60\text{ V}$	BDV67B	-	-		
			$V_{CB}= 70\text{ V}$	BDV67C	-	-		
			$V_{CB}= 80\text{ V}$	BDV67D	-	-		
V_{CEO}	Collector-emitter Breakdown Voltage (*)	$I_C= 30\text{ mA}, I_B= 0$		BDV67	60	-	-	V
				BDV67A	80	-		
				BDV67B	100	-		
				BDV67C	120	-		
				BDV67D	150	-		
h_{FE}	DC Current Gain (*)	$V_{CE}= 3\text{ V}, I_C= 1\text{ A}$		BDV67	-	3000	-	-
		$V_{CE}= 3\text{ V}, I_C= 10\text{ A}$		BDV67A	1000	-	-	
		$V_{CE}= 3\text{ V}, I_C= 16\text{ A}$		BDV67B		-	-	
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C= 10\text{ A}, I_B= 40\text{ mA}$		BDV67C	-	-	2	V
				BDV67D				
				BDV67				
				BDV67A				
				BDV67B				

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ELECTRICAL CHARACTERISTICS

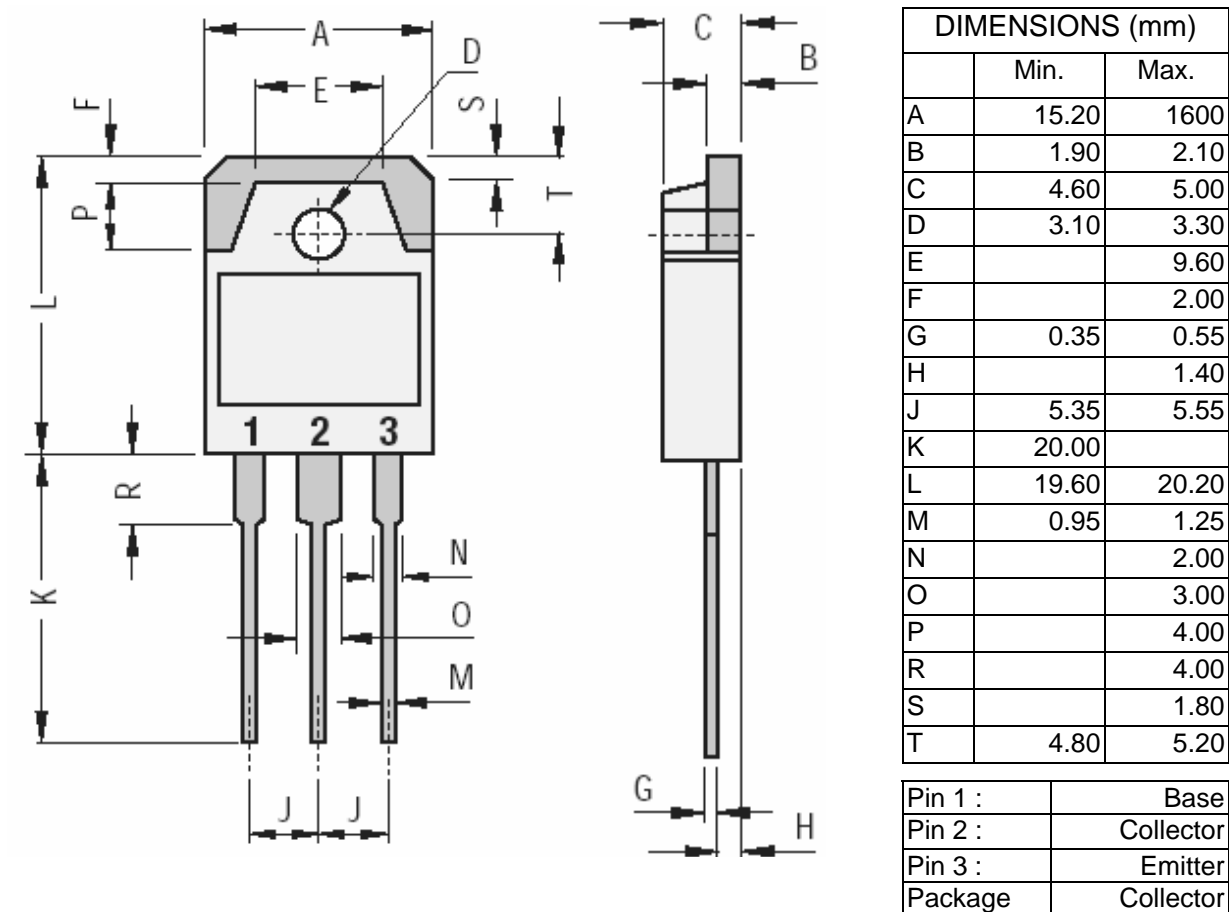
TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit	
V_{BE}	Base-Emitter Voltage (*)	$V_{CE}= 3 \text{ V}, I_C= 10 \text{ A}$	BDV67	-	-	2,5	V
			BDV67A				
			BDV67B				
			BDV67C				
			BDV67D				
V_F	Diode forward voltage	$I_F= 10 \text{ A}$	BDV67	-	-	3	V
			BDV67A				
			BDV67B				
			BDV67C				
			BDV67D				
C_c	Collector capacitance	$I_E= 0 \text{ A}, V_{CB}= 10 \text{ V}$ $f= 1 \text{ MHz}$	BDV67	-	300	-	pF
			BDV67A				
			BDV67B				
			BDV67C				
			BDV67D				

(*) Pulse Width $\approx 300 \mu\text{s}$, Duty Cycle $\angle 2.0\%$

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MECHANICAL DATA CASE TO3PN Non Isolated Plastic Package



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